PI

(a) Dopant requirements:

type: acceptor, group III atoms

Concentration: $N_A = p_o = 8 \times 10^{14} \text{ cm}^3$ minority carriers are electrons.

(b) - H

Carrier Contributions to current: holes from p to n regions electrons from n to p regions Current is diffusion type.

PZ

$$V_{I} = R_{1}I_{D2} + V_{D2} + V_{D3} + V_{D1}$$

$$V_{D1} = R_{2}I_{R2} = R_{2}(I_{D2} - I_{D1})$$

$$I_{D1} = I_{s}(e^{V_{D1}/V_{7}} - 1)$$

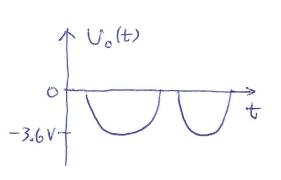
$$I_{D2} = I_{D3} = I_{s}(e^{V_{D2}/V_{7}} - 1)$$

$$V_{D2} = V_{D3}$$

P3

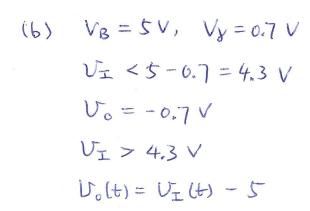
(a)
$$V_s > 2V_8$$
, D_3 and D_4 on $V_0 = -V_5 + V_8$
 V_0 , $peak = -5 + 1.4 = -3.6V$
 $V_5 < -2V_8$, D_1 and D_2 on $V_0 = V_5 + 2V_8$

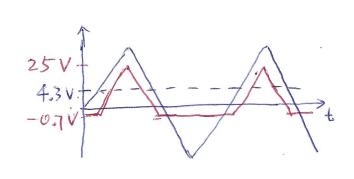
Vo, peak = -5+1.4 = -3.6V



(b) Capacitor is connected in parallel to RL $Vripple = V_{M} \frac{T_{P}}{R_{L}C} = \frac{V_{M}}{2fR_{L}C}$

 $\frac{P4}{(a)} \cdot V_{I} - V_{B} < -V_{Y}$ or $V_{I} < V_{B} - V_{Y}$ diode on $V_{O}(t) = -V_{Y}$ $V_{I} > V_{B} - V_{Y}$ diode of $V_{O}(t) = U_{I}(t) - V_{B}$





P5

(a) Initial Volo) = 0

when VB - UI > Vy

or VI < VB-Vy, diode on

capacitor charging

Vc = VB - Vy - VI

VC, max = VB - Vy - VI, min

When UI > VI, min, diode off, capacitor discharging slowly

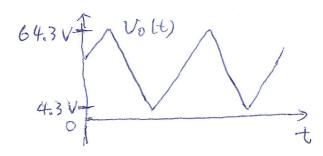
Vc = Vc, max and in steady state

Volt) = UI(t) + Vc, max

(b) VI, min = -30 V

Vc, max = VB - Vx - VI, min = 5 - 0.7 - (-30) = 34.3 V

Vo(t) = V_1(t) + 34.3 V



$$\frac{P_6}{V_2 = V_{20} + r_2 I_2}$$

$$\frac{V_2 - V_I}{R_0} + \frac{V_2 - V_{20}}{r_2} + \frac{V_2}{RL} = 0$$

$$\frac{V_2 - 20}{100} + \frac{V_2 - 10}{10} + \frac{V_2}{200} = 0$$

$$\Rightarrow V_2 = \frac{240}{23} V$$

$$I_2 = \frac{V_2 - V_{20}}{r_{\pi}} = \frac{1}{23} A$$

$$P_2 = V_2 I_2 = (V_{20} + r_2 I_2) I_2$$

$$= 0.454 V$$